

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

**Applicant(s):** Hussein I. Hanafi, et al.

**Examiner:** Unassigned

**Serial No:** To be assigned

**Art Unit:** Unassigned

**Filed:** Herewith

**Docket:** YOR2002018US2 (15790A)

**For:** LOW RESISTANCE T-GATE MOSFET  
DEVICE USING A DAMASCENE GATE  
PROCESS AND AN INNOVATIVE  
OXIDE REMOVAL ETCH

**Dated:** September 11, 2003

Commissioner for Patents  
United States Patent and Trademark Office  
P.O. Box 1450  
Alexandria, VA 22313-1450

**PRELIMINARY AMENDMENT**

Sir:

In connection with filing the above-identified patent application under 37  
C.F.R. §1.53(b), applicants submit the following amendments and remarks for entry of  
record in the above-identified patent application.

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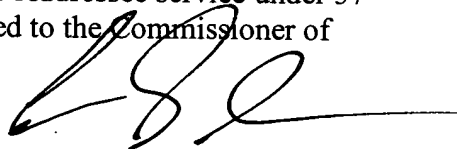
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Dated: September 11, 2003

  
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Leslie S. Szivos, Ph.D.